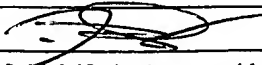


INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary) PTO Form 1449	Atty Docket No. 112857-534	Application No. 104512131
	Applicant Okuyama et al.	
	Filing Date October 21, 2004	Group 2Y15 Unknown

U.S. PATENT DOCUMENTS						
Examiner's Initials	Document Number	Publication Date	Inventor	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS								
Examiner's Initials	Document Number	Publication Date	Country	Class	Subclass	Translation		
						Yes	No	
②	06-045648	02-18-1994	Japan					
	09-129974	05-16-1997	Japan					
	11-026883	01-29-1999	Japan					
	2002-100805	04-05-2002	Japan					
②	2002-261327	09-13-2002	Japan					

Examiner's Initials	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
②	Tachibana, K. et al., "Selective growth of InGaN quantum dot structures and their microphotoluminescence at room temperature," Applied Physics Letters, 29 May, 2000, Vol. 76, No. 22, pp. 3212-3214.

Examiner: 	Date Considered: 12/19/04
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

2/5

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary) PTO Form 1449	Atty Docket No. 112857-534	Application No. 10/512,131
	Applicant Okuyama et al.	
	Filing Date 10/21/2004	Group 2815 Unknown

U.S. PATENT DOCUMENTS						
Examiner's Initials	Document Number	Publication Date	Inventor	Class	Subclass	Filing Date If Appropriate
D	5,177,405	01-05-93	Kusuda et al.			
	5,727,008	03-10-98	Koga			
	5,732,098	03-24-98	Nisitani			
	5,814,839	09-29-98	Hosoba			
	5,828,088	10-27-98	Mauk			
	5,981,977	11-09-99	Furukawa et al.			
	6,252,255	06-26-01	Ueta et al.			
	6,320,209	11-20-01	Hata et al.			

FOREIGN PATENT DOCUMENTS							
Examiner's Initials	Document Number	Publication Date	Country	Class	Subclass	Translation	
						Yes	No
D	56-92577	07-27-81	Japan				
	57-45583	03-15-82	Japan				
	57-52071	03-27-82	Japan				
	57-52072	03-27-82	Japan				
	57-52073	03-27-82	Japan				
	58-50577	03-25-83	Japan				
	61-156780	07-16-86	Japan				
	63-188938	08-04-88	Japan				
	2-263668	10-26-90	Japan				
	03-035568	02-15-91	Japan				
	06-067044	03-11-94	Japan				
	07-199829	04-08-95	Japan				
	08-008217	01-12-96	Japan				
	08-255929	10-01-96	Japan				
	09-199419	07-31-97	Japan				
	10-125929	05-05-98	Japan				
	10-265297	10-06-98	Japan				
	10-270801	10-09-98	Japan				

Examiner: 

Date Considered: 12/19/06

*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary) PTO Form 1449	Atty Docket No. 112857-534	Application No. 10/512,131
	Applicant Okuyama et al.	
	Filing Date 10/21/2004	Group 2815 Unknown

FOREIGN PATENT DOCUMENTS								
Examiner's Initials		Document Number	Publication Date	Country	Class	Subclass	Translation	
							Yes	No
<i>D</i>		10-312971	11-24-98	Japan				
		10-321910	12-04-98	Japan				
		11-075019	03-16-99	Japan				
		11-177138	07-02-99	Japan				
		11-238687	08-31-99	Japan				
		11-251253	09-17-99	Japan				
		11-274568	10-08-99	Japan				
		11-312840	11-09-99	Japan				
		11-346004	12-14-99	Japan				
		11-514136	11-30-99	Japan				
		2000-068593	03-03-00	Japan				
		2000-012976	01-14-00	Japan				
		2000-150391	05-30-00	Japan				
		2000-183451	06-30-00	Japan				
		2000-223417	08-11-00	Japan				
		2000-332343	11-30-00	Japan				
		2001-085738	03-30-01	Japan				
		2001-217503	08-10-01	Japan				
		2002-185660	12-12-02	Japan				
		WO 97/44612	11-27-97	PCT				
<i>D</i>		WO 02/07231	01-24-02	PCT				

Examiner's Initials	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
<i>D</i>	Zheleva et al., "Pendeo-epitaxy - a new approach for lateral growth of gallium nitride structures," MRS Internet J. Nitride Semicond. Res. 4S1, G3.38 (1999).
<i>D</i>	Kapolnek et al., "Spatial control of InGaN luminescence by MOCVD selective epitaxy," Journal of Crystal Growth, 189/190 (1998) pp. 83-86.
<i>D</i>	Wang et al., "Fabrication of nanoscale structures of InGaN by MOCVD lateral overgrowth," Journal of Crystal Growth 197 (1999), pp. 48-53.

Examiner: <i>[Signature]</i>	Date Considered: 12/18/06
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

